

Subject card

Subject name and code	Physics of semiconductor devices, PG_00037293								
Field of study	Technical Physics								
Date of commencement of studies	October 2021		Academic year of realisation of subject			2023/2024			
Education level	first-cycle studies		Subject group			Optional subject group Subject group related to scientific research in the field of study			
Mode of study	Full-time studies		Mode of delivery			at the university			
Year of study	3		Language of instruction			Polish			
Semester of study	5		ECTS credits			5.0			
Learning profile	general academic profile		Assessment form			exam			
Conducting unit	Department of Physic	Phenomena -> Faculty of Applied Physics and Mathematics							
Name and surname	Subject supervisor Teachers		dr hab. inż. Jędrzej Szmytkowski						
of lecturer (lecturers)			dr hab. inż. Je	wski					
Lesson types and methods of instruction	Lesson type	Lecture	Tutorial	Laboratory	Projec	t	Seminar	SUM	
	Number of study hours	30.0	30.0	0.0	0.0		0.0	60	
	E-learning hours included: 0.0								
Learning activity and number of study hours	Learning activity	g activity Participation ir classes including plan		Participation in consultation hours		Self-study		SUM	
	Number of study 60 hours			5.0		60.0		125	
Subject objectives	The aim of this course is to understand fundamental physics of semiconductors and devices based on semiconductors.								
Learning outcomes	Course outcome		Subject outcome			Method of verification			
	K6_W02					[SW1] Assessment of factual knowledge			
	K6_W07		Student knows how semiconductor devices work.			[SW1] Assessment of factual knowledge			
	K6_U01		Student knows how to use literature and databases in semiconductors and semisonductor devices			[SU2] Assessment of ability to analyse information			
Subject contents	Introduction to solid state physics (structure of crystalline solids, types of chemical bonds in solids, phonons, Fermi-Dirac and Bose-Einstein statistics, Fermi level in metals, electrical conduction in metals, band structure of solids, effective mass). Introduction to semiconductors (electronic hole, Fermi level in semiconductors, direct and indirect energy gap, equilibrium concentration, intrinsic and extrinsic semiconductors, donors and acceptors, generation and recombination of charge carriers, Hall effect, p-n junction). Introduction to semiconductor electrodynamics (mobility of carries, drift and diffusion equations, Poisson equation, continuity equation, space charge, dielectric relaxation, ambipolar transport equation, Shockley equation). Semiconductor devices (photoresistor, Hall effect sensor, magnetoresistor, thermistor, varistor, diode, varicap, Zener diode, Esaki diode, Schottky diode, photovoltaic cell, photodiode, LED, semiconductor laser, bipolar junction transistor, field-effect transistor JFET, field-effect transistor MOSFET, thyristor). Injection, termionic and optical effects in semiconductor devices.MOS capacitor, Charge-coupled device (CCD). Integrated circuits. Semiconductor nanostructures and devices based on them.								
Prerequisites and co-requisites	Completed courses in "Electricity and magnetism" and "Introduction to modern physics"								
Assessment methods and criteria	Subject passing criteria		Passing threshold			Percentage of the final grade			
	Exercises		50.0%			40.0%			
	Written exam		50.0%			60.0%			

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Recommended reading	Basic literature	C. Kittel "Introduction to solid state physics", PWN A. van der Ziel "Fundaments of solid state electronics" WNT J. Hennel "Introduction to semiconductor elektronics" WNT			
	Supplementary literature	A.K. Jonscher "Fundaments of semiconductor devices" WNT			
	eResources addresses	Adresy na platformie eNauczanie:			
		Fizyka przyrządów półprzewodnikowych - Moodle ID: 33946 https://enauczanie.pg.edu.pl/moodle/course/view.php?id=33946			
Example issues/ example questions/ tasks being completed	Electronic structure of solid states				
	2. Intrinsic and extrinsic semiconductors 3. Diode 4. Transistor				
	5. Laser diode				
Work placement	Not applicable				

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